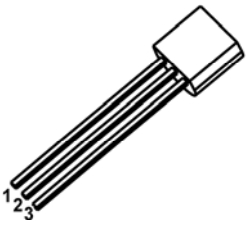
ShenzhenTaimaoTechnology Co.,Ltd.

TO-92 Plastic-Encapsulate Transistors

TO – 92

1. EMITTER
2. BASE
3. COLLECTOR



2N6520 TRANSISTOR (PNP)

FEATURES

- Complement to 2N6517

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-350	V
V_{CEO}	Collector-Emitter Voltage	-350	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-0.5	A
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	℃/W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~+150	℃

ELECTRICAL CHARACTERISTICS (T_a=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=- 0.1mA,I_E=0	-350			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$*	I_C=-1mA,I_B=0	-350			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-0.01mA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-250V,I_E=0			-0.05	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-0.05	μA
DC current gain	h_{FE}	V_{CE}=-10V, I_C=-1mA	20			
		V_{CE}=-10V, I_C=-10mA	30			
		V_{CE}=-10V, I_C=-30mA	30		200	
		V_{CE}=-10V, I_C=-50mA	20		200	
		V_{CE}=-10V, I_C=-100mA	15			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-10mA,I_B=-1mA			-0.3	V
		I_C=-20mA,I_B=-2mA			-0.35	V
		I_C=-30mA,I_B=-3mA			-0.5	V
		I_C=-50mA,I_B=-5mA			-1	V
Base-emitter saturation voltage	$V_{BE\ (sat)}$	I_C=-10mA,I_B=-1mA			-0.75	V
		I_C=-20mA,I_B=-2mA			-0.85	V
		I_C=-30mA,I_B=-3mA			-0.9	V
Base-emitter voltage	V_{BE}	V_{CE}=-10V, I_C=-100mA			-2	V
Transition frequency	f_T*	V_{CE}=-20V,I_C=-10mA,f=20MHz	40		200	MHz

*Pulse test: pulse width ≤300μs, duty cycle≤ 2.0%.